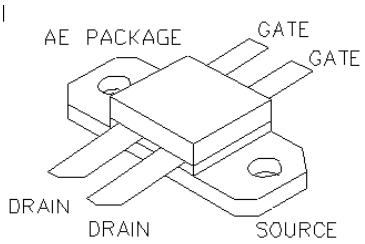
polyfet rf devices

SE701

General Description

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Militry Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"™ process features low feedback and output capacitances resulting in high F_t transistors with high input impedance and high efficiency.



SILICON GATE ENHANCEMENT MODE

RF POWER VDMOS TRANSISTOR

45.0 Watts Push - Pull

Package Style AE

HIGH EFFICIENCY, LINEAR
HIGH GAIN, LOW NOISE

ABSOLUTE MAXIMUM RATINGS (T = 25 °C)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
110 Watts	1.40 °C/W	200 °C	-65 °C to 150 °C	6.5 A	70V	70V	20 V

RF CHARACTERISTICS (45.0 WATTS OUTPUT)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	10			dB	Idq = 0.40 A, Vds = 28.0 V, F = 500 MHz
η	Drain Efficiency		55		%	Idq = 0.40 A, Vds = 28.0 V, F = 500 MHz
VSWR	Load Mismatch Tolerance			20:1	Relative	Idq = 0.40 A, Vds = 28.0 V, F = 500 MHz

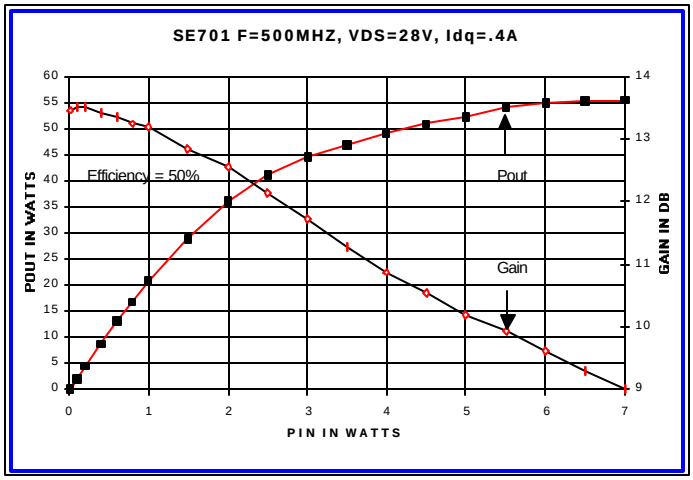
ELECTRICAL CHARACTERISTICS (EACH SIDE)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	65			V	Ids = 20.00 mA, Vgs = 0V
Idss	Zero Bias Drain Current			1.0	mA	Vds = 28.0 V, Vgs = 0V
Igss	Gate Leakage Current			1	uA	Vds = 0V Vgs = 30V
Vgs	Gate Bias for Drain Current	1		7	V	Ids = 0.10 A, Vgs = Vds
gM	Forward Transconductance		1.2		Mho	Vds = 10V, Vgs = 5V
Rdson	Saturation Resistance		0.85		Ohm	Vgs = 20V, Ids = 2.50 A
Idsat	Saturation Current		7.00		Amp	Vgs = 20V, Vds = 10V
Ciss	Common Source Input Capacitance		50.0		pF	Vds = 28.0 Vgs = 0V, F = 1 MHz
Crss	Common Source Feedback Capacitance		3.0		pF	Vds = 28.0 Vgs = 0V, F = 1 MHz
Coss	Common Source Output Capacitance		32.0		pF	Vds = 28.0 Vgs = 0V, F = 1 MHz

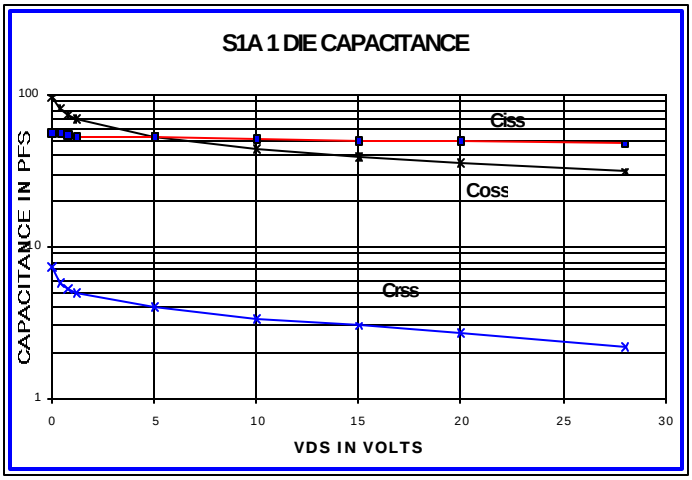
1110 Avenida Acaso, Camarillo, Ca 93012 Tel:(805) 484-4210 FAX: (805) 484-3393 EMAIL:Sales@polyfet.com URL:www.polyfet.com

SE701

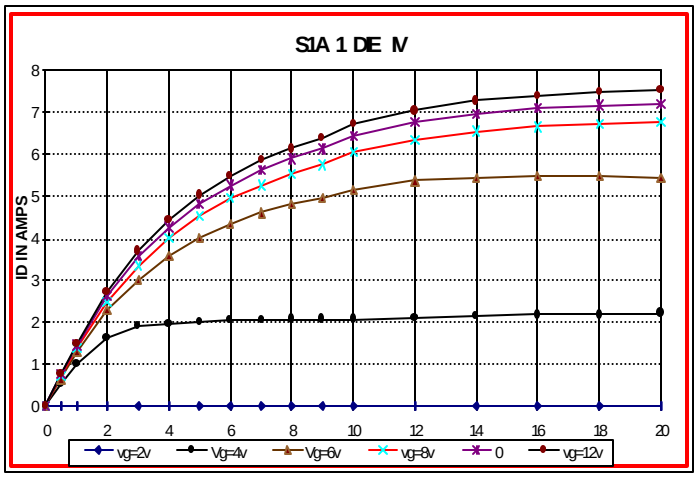
POUT VS PIN GRAPH



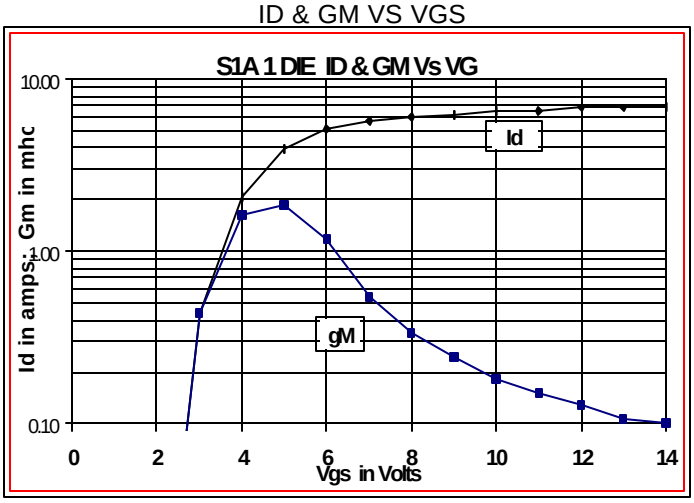
CAPACITANCE VS VOLTAGE



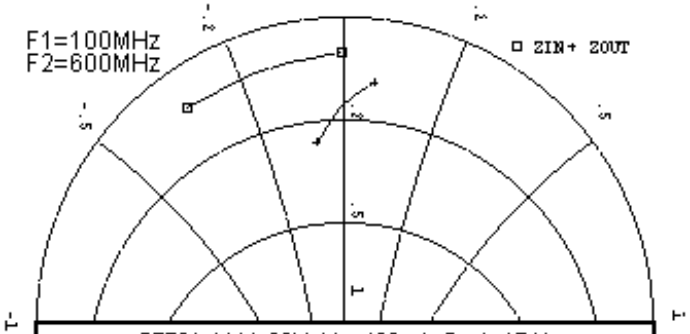
IV CURVE



ID & GM VS VGS

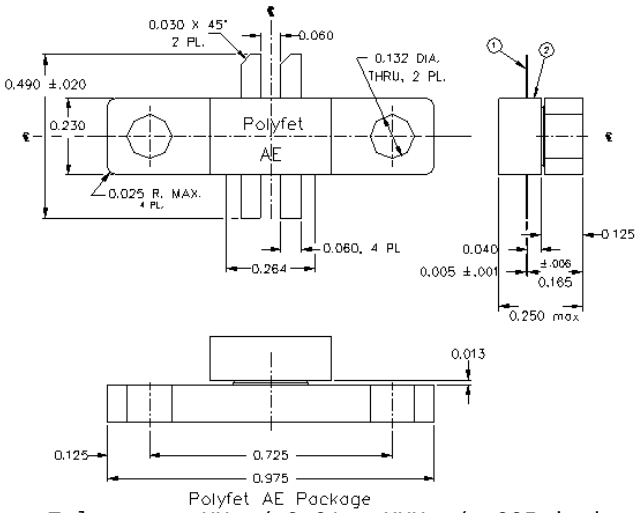


Zin Zout



SE701 Vdd=28V Idq=400mA Pout=45W						
Freq(MHz)	100	200	300	400	500	600
Zin	8.0	7.4	7.2	7.0	6.6	6.2
	-j32.0	-j18.0	-j10.0	-j6.0	-j2.8	-j0.2
Zout	25.6	20	17.4	14.8	13	12
	-j7.0	-j2.8	-j0.8	j2.0	j4.6	j6.4

PACKAGE DIMENSIONS IN INCHES



Tolerance .XX +/-0.01 .XXX +/-.005 inches

POLYFET RF DEVICES REVISION 03/28/2001

1110 Avenida Acaso, Camarillo, Ca 93012 Tel:(805) 484-4210 FAX: (805) 484-3393 EMAIL:Sales@polyfet.com URL:www.polyfet.com